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Editorial

This volume contains the proceedings of the 10th edition of the International Conference on Simulation of Semiconductor Processes and Devices (SISPAD 2004), held in Munich, Germany, on September 2-4, 2004. The SISPAD conference is annually organized, with alternating venues in Europe, Japan, and North America. SISPAD 2002 took place in Kobe, Japan, and SISPAD 2003 was held in Boston, MA, USA. This year's SISPAD was organized by the Institute for Physics of Electrotechnology, Munich University of Technology.

Like the previous meetings, SISPAD 2004 provided a world-wide forum for the presentation and discussion of recent advances and developments in the theoretical description, physical modeling and numerical simulation and analysis of semiconductor fabrication processes, device operation and system performance. The variety of topics covered by the conference contributions reflects the physical effects and technological problems encountered in consequence of the progressively shrinking device dimensions and the ever-growing complexity in device technology. The rapid progress made in this field necessitates continuous advances in the physical models and simulation tools, which constitute the basis for predictive simulation on all descriptive levels from atomistic models up to full system macromodels, as they are offered by state-of-the-art TCAD platforms.

The conference program included 7 invited plenary lectures and 82 contributed papers for oral or poster presentation, which were carefully selected out of a total of 151 abstracts submitted from 14 countries around the world.

The proceedings volume contains eight-page manuscripts as received from the invited authors and four-page extended abstracts of the contributed papers. All of them were reproduced as submitted, and therefore the responsibility for the contents rests exclusively with the authors. We express our sincere appreciation to them for respecting the guidelines and for their effort to provide high-quality contributions.

The editors wish to thank the members of the Technical Program Committee for proposing the invited speakers and for the careful selection of the contributed papers. We gratefully acknowledge the support of all people who helped us to make SISPAD 2004 a success.

Gerhard Wachutka
Conference Chair

Gabriele Schrag
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